

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Applicant(s)

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Filing Date

Group Art Unit

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SW	A	6,137,130	10/2000	SUNG	257	306	
SW	B	6,136,646	10/2000	LINLIU et al.	438	255	
SW	C	US 2002/0037644A1	03/2002	RHA et al.	438	656	
SW	D	6,180,970 B1	01/2001	HWANG et al.	257	295	
SW	E	6,239,461 B1	05/2001	LEE	257	306	
SW	F	5,296,095	03/1994	NABESHIMA et al.	156	662	
SW	G	5,726,499	03/1998	IRINODA	257	774	
SW	H	6,348,709 B1	02/2002	GRAETTINGER et al.	257	311	

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
SW	I	5-13750	01/22/1993	JAPAN				
SW	J	7-297280	11/10/1995	JAPAN				
SW	K	JP407297280A	10/1995	JAPAN				
SW	L	JP2000-040805A	02/2000	JAPAN				
SW	M	2001-0055403	07/04/2001	REPUBLIC OF KOREA				

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SW	N	Miyashita, T. et al., "A Novel Bit-Line Process using Ploy-Si Masked Dual-Damascene (PMDD) for 0.13 microm DRAMs and Beyond", in Electron Devices Mtg, 2000, IEDM Techn. Digest, 12/10/2000-12/13/2000, San Francisco, CA (USA) (INSPEC Accession No: 6880863).

EXAMINER

*[Signature]*

DATE CONSIDERED

7/9/04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.